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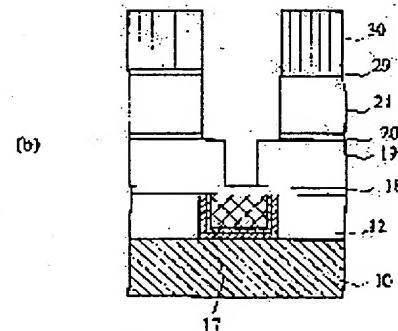
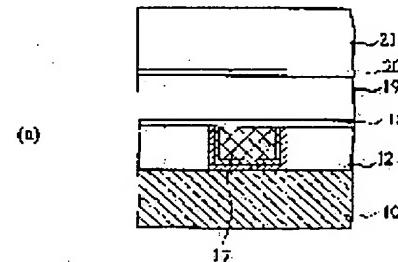
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(54) MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To improve interface adhesion between a low dielectric constant film and a protection film without damaging excellent dielectric properties of an organic low dielectric constant material, flatness and gap filling characteristics.

SOLUTION: A resist 30 is removed by ashing employing plasma using mixture gas containing nitrogen and hydrogen. The content of hydrogen in mixture gas is 20% or less in volume base.



LEGAL STATUS

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